Catherine Bougerol

List of Publications by Year
in descending order

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288 papers	8,837 citations	41344 49 h-index	56724 83 g-index
293 all docs	293 docs citations	293 times ranked	5658 citing authors

#	Article	IF	Citations
1	Transport properties of a thin GaN channel formed in an Al_{0.9}Ga_{0.1}N/GaN heterostructure grown on AlN/sapphire template. Journal of Applied Physics, 2022, 131, 124501.	2.5	2
2	Solubility Limit of Ge Dopants in AlGaN: A Chemical and Microstructural Investigation Down to the Nanoscale. ACS Applied Materials & Interfaces, 2021, 13, 4165-4173.	8.0	7
3	Improvement of critical temperature of niobium nitride deposited on 8-inch silicon wafers thanks to an AlN buffer layer. Superconductor Science and Technology, 2021, 34, 045002.	3.5	4
4	Dualâ€Color Emission from Monolithic mâ€Plane Coreâ€“Shell InGaN/GaN Quantum Wells. Advanced Photonics Research, 2021, 2, 2000148.	3.6	5
5	Comprehensive model toward optimization of SAG In-rich InGaN nanorods by hydride vapor phase epitaxy. Nanotechnology, 2021, 32, 155601.	2.6	0
6	The role of surface diffusion in the growth mechanism of III-nitride nanowires and nanotubes. Nanotechnology, 2021, 32, 085606.	2.6	7
7	Toward Crack-Free Coreâ€“Shell GaN/AlGaN Quantum Wells. Crystal Growth and Design, 2021, 21, 6504-6511.	3.0	7
8	Correlative investigation of Mg doping in GaN layers grown at different temperatures by atom probe tomography and off-axis electron holography. Nanotechnology, 2020, 31, 045702.	2.6	12
9	UV Emission from GaN Wires with m-Plane Coreâ€“Shell GaN/AlGaN Multiple Quantum Wells. ACS Applied Materials & Interfaces, 2020, 12, 44007-44016.	8.0	16
10	Carrier dynamics near a crack in GaN microwires with AlGaN multiple quantum wells. Applied Physics Letters, 2020, 117, .	3.3	10
11	Controlling the shape of a tapered nanowire: lessons from the Burton-Cabrera-Frank model. Nanotechnology, 2020, 31, 274004.	2.6	3
12	Role of Underlayer for Efficient Coreâ€“Shell InGaN QWs Grown on m-plane GaN Wire Sidewalls. ACS Applied Materials & Interfaces, 2020, 12, 19092-19101.	8.0	18
13	Formation of voids in selective area growth of InN nanorods in SiN_x on GaN templates. Nano Futures, 2020, 4, 025002.	2.2	5
14	Three-dimensional measurement of Mg dopant distribution and electrical activity in GaN by correlative atom probe tomography and off-axis electron holography. Journal of Applied Physics, 2020, 127, 065702.	2.5	15
15	Internal quantum efficiency of AlGaN/AlN quantum dot superlattices for electron-pumped ultraviolet sources. Nanotechnology, 2020, 31, 505205.	2.6	6
16	Optical and structural analysis of ultra-long GaAs nanowires after nitrogen-plasma passivation. Nano Express, 2020, 1, 020019.	2.4	8
17	High Lateral Breakdown Voltage in Thin Channel AlGaN/GaN High Electron Mobility Transistors on AlN/Sapphire Templates. Micromachines, 2019, 10, 690.	2.9	28
18	Si Doping of Vaporâ€“Liquidâ€“Solid GaAs Nanowires: n-Type or p-Type?. Nano Letters, 2019, 19, 4498-4504.	9.1	26

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19	Design and implementation of bound-to-quasibound GaN/AlGaN photovoltaic quantum well infrared photodetectors operating in the short wavelength infrared range at room temperature. Journal of Applied Physics, 2019, 125, 174505.	2.5	10
20	Selective growth of ordered hexagonal InN nanorods. CrystEngComm, 2019, 21, 2702-2708.	2.6	13
21	Improvement of the critical temperature of NbTiN films on III-nitride substrates. Superconductor Science and Technology, 2019, 32, 035008.	3.5	10
22	Compositional control of homogeneous InGaN nanowires with the In content up to 90%. Nanotechnology, 2019, 30, 044001.	2.6	12
23	Dopant radial inhomogeneity in Mg-doped GaN nanowires. Nanotechnology, 2018, 29, 255706.	2.6	19
24	High spatial resolution correlated investigation of Zn segregation to stacking faults in ZnTe/CdSe nanostructures. Applied Physics Letters, 2018, 112, .	3.3	4
25	GaN/AlGaN Photovoltaic Quantum Well Infrared Photodetector at 2.3 Î¼m. , 2018, , .		0
26	Green Electroluminescence from Radial m-Plane InGaN Quantum Wells Grown on GaN Wire Sidewalls by Metalâ€“Organic Vapor Phase Epitaxy. ACS Photonics, 2018, 5, 4330-4337.	6.6	26
27	Circumventing the miscibility gap in InGaN nanowires emitting from blue to red. Nanotechnology, 2018, 29, 465602.	2.6	22
28	Influence of Silicon on the Nucleation Rate of GaAs Nanowires on Silicon Substrates. Journal of Physical Chemistry C, 2018, 122, 19230-19235.	3.1	15
29	Near-UV narrow bandwidth optical gain in lattice-matched IIIâ€“nitride waveguides. Japanese Journal of Applied Physics, 2018, 57, 090305.	1.5	3
30	Self-catalyzed GaAs nanowires on silicon by hydride vapor phase epitaxy. Nanotechnology, 2017, 28, 125602.	2.6	12
31	Thin-Wall GaN/InAlN Multiple Quantum Well Tubes. Nano Letters, 2017, 17, 3347-3355.	9.1	9
32	Effect of Al incorporation in nonpolar m -plane GaN/AlGaN multi-quantum-wells using plasma-assisted molecular-beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600849.	1.8	6
33	Effect of Ge-doping on the short-wave, mid- and far-infrared intersubband transitions in GaN/AlGaN heterostructures. Semiconductor Science and Technology, 2017, 32, 125002.	2.0	6
34	InGaN/GaN nanowire flexible light emitting diodes and photodetectors. , 2017, , .		1
35	Flexible Light Emitting Diodes Based on Nitride Nanowires. , 2017, , .		0
36	Short-wavelength, mid- and far-infrared intersubband absorption in nonpolar GaN/Al(Ga)N heterostructures. Japanese Journal of Applied Physics, 2016, 55, 05FG05.	1.5	9

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37	Dependence of the photovoltaic performance of pseudomorphic InGaN/GaN multiple-quantum-well solar cells on the active region thickness. Applied Physics Letters, 2016, 108, .	3.3	24
38	GaN Rods Grown on Si by SAG-HVPE toward GaN HVPE/InGaN MOVPE Core/Shell Structures. Crystal Growth and Design, 2016, 16, 2509-2513.	3.0	8
39	InGaN nanowires with high InN molar fraction: growth, structural and optical properties. Nanotechnology, 2016, 27, 195704.	2.6	19
40	Flexible Photodiodes Based on Nitride Core/Shell pâ€“n Junction Nanowires. ACS Applied Materials & Interfaces, 2016, 8, 26198-26206.	8.0	66
41	Spontaneous formation of GaN/AlN coreâ€“shell nanowires on sapphire by hydride vapor phase epitaxy. Journal of Crystal Growth, 2016, 454, 1-5.	1.5	5
42	Self-catalyzed growth of GaAs nanowires on silicon by HVPE. , 2016, , .		1
43	Composition Analysis of III-Nitrides at the Nanometer Scale: Comparison of Energy Dispersive X-ray Spectroscopy and Atom Probe Tomography. Nanoscale Research Letters, 2016, 11, 461.	5.7	17
44	Chemical composition fluctuations and strain relaxation in InGaN nanowires: The role of the metal/nitrogen flux ratio. Materials Science in Semiconductor Processing, 2016, 55, 79-84.	4.0	8
45	Interfacial chemistry in a ZnTe/CdSe superlattice studied by atom probe tomography and transmission electron microscopy strain measurements. Journal of Microscopy, 2016, 262, 178-182.	1.8	10
46	Flexible White Light Emitting Diodes Based on Nitride Nanowires and Nanophosphors. ACS Photonics, 2016, 3, 597-603.	6.6	89
47	Effect of doping on the far-infrared intersubband transitions in nonpolarm-plane GaN/AlGaN heterostructures. Nanotechnology, 2016, 27, 145201.	2.6	16
48	Nonpolarm-plane GaN/AlGaN heterostructures with intersubband transitions in the 5â€“10 THz band. Nanotechnology, 2015, 26, 435201.	2.6	26
49	Atomic arrangement at ZnTe/CdSe interfaces determined by high resolution scanning transmission electron microscopy and atom probe tomography. Applied Physics Letters, 2015, 106, 051904.	3.3	15
50	Investigation of Photovoltaic Properties of Single Coreâ€“Shell GaN/InGaN Wires. ACS Applied Materials & Interfaces, 2015, 7, 21898-21906.	8.0	39
51	Intersubband transitions in nonpolar GaN/Al(Ga)N heterostructures in the short- and mid-wavelength infrared regions. Journal of Applied Physics, 2015, 118, 014309.	2.5	26
52	Flexible Light-Emitting Diodes Based on Vertical Nitride Nanowires. Nano Letters, 2015, 15, 6958-6964.	9.1	172
53	The influence of AlN buffer over the polarity and the nucleation of self-organized GaN nanowires. Journal of Applied Physics, 2015, 117, .	2.5	55
54	Complete solid state lighting (SSL) line at CEA LETI. Proceedings of SPIE, 2014, , .	0.8	1

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55	High-T_c Superconducting Cuprates, (Ce,Y)_sO_{2s-2}Sr₂(Cu_{2.75}Mo_{0.25})O_{6+Î´}: T_c-increase with apical Cu-O decrease at constant Cu-O planar distance. Journal of Physics: Conference Series, 2014, 507, 012031.	0.4	2
56	Effect of the quantum well thickness on the performance of InGaN photovoltaic cells. Applied Physics Letters, 2014, 105, .	3.3	60
57	THz intersubband transitions in AlGaN/GaN multiâ€quantumâ€wells. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 761-764.	1.8	11
58	M-Plane GaN/InAlN Multiple Quantum Wells in Coreâ€“Shell Wire Structure for UV Emission. ACS Photonics, 2014, 1, 38-46.	6.6	42
59	Cu2ZnSn(S1â^'xSex)4 thin films for photovoltaic applications: Influence of the precursor stacking order on the selenization process. Journal of Alloys and Compounds, 2014, 588, 310-315.	5.5	19
60	Pseudo-square AlGaN/GaN quantum wells for terahertz absorption. Applied Physics Letters, 2014, 105, 131106.	3.3	25
61	Ultralong and Defect-Free GaN Nanowires Grown by the HVPE Process. Nano Letters, 2014, 14, 559-562.	9.1	58
62	Improved conversion efficiency of as-grown InGaN/GaN quantum-well solar cells for hybrid integration. Applied Physics Express, 2014, 7, 032301.	2.4	18
63	High-quality NbN nanofilms on a GaN/AlN heterostructure. AIP Advances, 2014, 4, 107123.	1.3	11
64	Metal organic vapour-phase epitaxy growth of GaN wires on Si (111) for light-emitting diode applications. Nanoscale Research Letters, 2013, 8, 61.	5.7	28
65	Optical properties of single ZnTe nanowires grown at low temperature. Applied Physics Letters, 2013, 103, .	3.3	20
66	Strain assisted inter-diffusion in GaN/AlN quantum dots. Journal of Applied Physics, 2013, 113, 034311.	2.5	14
67	Growth of IIâ€“VI ZnSe/CdSe nanowires for quantum dot luminescence. Journal of Crystal Growth, 2013, 378, 233-237.	1.5	7
68	Growth, structural and optical properties of AlGaN nanowires in the whole composition range. Nanotechnology, 2013, 24, 115704.	2.6	65
69	InGaN/GaN multipleâ€quantum well heterostructures for solar cells grown by MOVPE: case studies. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 350-354.	0.8	7
70	Intrinsic limits governing MBE growth of Ga-assisted GaAs nanowires on Si(111). Journal of Crystal Growth, 2013, 364, 118-122.	1.5	28
71	Probing alloy composition gradient and nanometer-scale carrier localization in single AlGaN nanowires by nanocathodoluminescence. Nanotechnology, 2013, 24, 305703.	2.6	24
72	Hydride VPE: the unexpected process for the fast growth of GaAs and GaN nanowires with record aspect ratio and polytypism-free crystalline structure. , 2013, , .		0

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73	Overdoped cuprates with high-temperature superconducting transitions. APL Materials, 2013, 1, .	5.1	11
74	Terahertz absorbing AlGaN/GaN multi-quantum-wells: Demonstration of a robust 4-layer design. Applied Physics Letters, 2013, 103, 091108.	3.3	27
75	Structural and optical properties of Al_x Ga_{1â€“x}N nanowires. Physica Status Solidi - Rapid Research Letters, 2013, 7, 868-873.	2.4	32
76	Photovoltaic Response of InGaN/GaN Multiple-Quantum Well Solar Cells. Japanese Journal of Applied Physics, 2013, 52, 08JH05.	1.5	22
77	Advanced semiconductor characterization with aberration corrected electron microscopes. Journal of Physics: Conference Series, 2013, 471, 012001.	0.4	3
78	Paramagnetic shift in thermally annealed CdxZn1â^'xSe quantum dots. New Journal of Physics, 2012, 14, 043038.	2.9	11
79	Catalyst-assisted hydride vapor phase epitaxy of GaN nanowires: exceptional length and constant rod-like shape capability. Nanotechnology, 2012, 23, 405601.	2.6	30
80	Growth mechanism and properties of InGaN insertions in GaN nanowires. Nanotechnology, 2012, 23, 135703.	2.6	67
81	In situ study of self-assembled GaN nanowires nucleation on Si(111) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2012, 100, .	3.3	47
82	Exciton-phonon coupling efficiency in CdSe quantum dots embedded in ZnSe nanowires. Physical Review B, 2012, 85, .	3.2	9
83	Extraction of the homogeneous linewidth of the spectrally diffusing line of a CdSe/ZnSe quantum dot embedded in a nanowire. Physical Review B, 2012, 86, .	3.2	6
84	Ultrafast Room Temperature Single-Photon Source from Nanowire-Quantum Dots. Nano Letters, 2012, 12, 2977-2981.	9.1	70
85	Growth, structural and optical properties of GaN/AlN and GaN/GaInN nanowire heterostructures. Physics Procedia, 2012, 28, 5-16.	1.2	4
86	Catalyst-free growth of high-optical quality GaN nanowires by metal-organic vapor phase epitaxy. Applied Physics Letters, 2011, 99, .	3.3	38
87	M-Plane Coreâ€“Shell InGaN/GaN Multiple-Quantum-Wells on GaN Wires for Electroluminescent Devices. Nano Letters, 2011, 11, 4839-4845.	9.1	186
88	Nordgauite, MnAl₂(PO₄)₂(F,OH)₂Â·5H₂O, a new mineral from the Hagendorf-SÃ¼d pegmatite, Bavaria, Germany: description and crystal structure. Mineralogical Magazine, 2011, 75, 269-278.	1.4	15
89	Subnanosecond spectral diffusion of a single quantum dot in a nanowire. Physical Review B, 2011, 84, .	3.2	44
90	Nucleation of GaN nanowires grown by plasma-assisted molecular beam epitaxy: The effect of temperature. Journal of Crystal Growth, 2011, 334, 177-180.	1.5	48

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91	Towards vertical coupling of CdTe/ZnTe quantum dots formed by a high temperature tellurium induced process. Journal of Crystal Growth, 2011, 335, 28-30.	1.5	27
92	Polarity of GaN nanowires grown by plasma-assisted molecular beam epitaxy on Si(111). Physical Review B, 2011, 84, .	3.2	95
93	Polarity determination in ZnSe nanowires by HAADF STEM. Journal of Physics: Conference Series, 2011, 326, 012044.	0.4	4
94	Measuring two dimensional strain state of AlN quantum dots in GaN nanowires by nanobeam electron diffraction. Journal of Physics: Conference Series, 2011, 326, 012047.	0.4	4
95	Vertical stacking of CdTeâˆ•ZnTe quantum dots formed by a fast tellurium induced process. , 2011, , .		0
96	Insertion of CdSe quantum dots in ZnSe nanowires: MBE growth and microstructure analysis. Journal of Crystal Growth, 2011, 323, 330-333.	1.5	4
97	Insertion of CdSe quantum dots in ZnSe nanowires: Correlation of structural and chemical characterization with photoluminescence. Journal of Applied Physics, 2011, 110, .	2.5	10
98	Structural and optical properties of InGaN/GaN nanowire heterostructures grown by PA-MBE. Nanotechnology, 2011, 22, 075601.	2.6	97
99	Structural properties of GaN nanowires and GaN/AlN insertions grown by molecular beam epitaxy. Journal of Physics: Conference Series, 2010, 209, 012010.	0.4	5
100	Single photons from single CdSe quantum dot embedded in ZnSe nanowire. International Journal of Nanotechnology, 2010, 7, 686.	0.2	1
101	Elastic strain relaxation in GaN/AlN nanowire superlattice. Physical Review B, 2010, 81, .	3.2	47
102	Influence of thermal annealing on the structural and optical properties of GaN/AlN quantum dots. Physica Status Solidi (B): Basic Research, 2010, 247, 1675-1678.	1.5	5
103	Epitaxial growth of ZnSe and ZnSe/CdSe nanowires on ZnSe. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1526-1529.	0.8	12
104	Growth mechanism of catalystâ€free [0001] GaN and AlN nanowires on Si by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2246-2248.	0.8	7
105	Subnanosecond spectral diffusion measurement using photon correlation. Nature Photonics, 2010, 4, 696-699.	31.4	123
106	Optical spectroscopy of cubic GaN in nanowires. Applied Physics Letters, 2010, 97, .	3.3	19
107	Reversed polarized emission in highly strained<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>a</mml:mi></mml:math>-plane GaN/AlN multiple quantum wells. Physical Review B, 2010, 82, .	3.2	8
108	Characterization of spin-state tuning in thermally annealed semiconductor quantum dots. Physical Review B, 2010, 82, .	3.2	12

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109	Quantum Transport in GaN/AlN Double-Barrier Heterostructure Nanowires. Nano Letters, 2010, 10, 3545-3550.	9.1	71
110	Ordering of Pd²⁺ and Pd⁴⁺ in the Mixed-Valent Palladate KPd₂O₃. Inorganic Chemistry, 2010, 49, 1295-1297.	4.0	19
111	The structural properties of GaN/AlN coreâ€“shell nanocolumn heterostructures. Nanotechnology, 2010, 21, 415702.	2.6	73
112	Coulsellite, CaNa3AlMg3F14, a rhombohedral pyrochlore with 1:3 ordering in both A and B sites, from the Cleveland Mine, Tasmania, Australia. American Mineralogist, 2010, 95, 736-740.	1.9	9
113	Molecular beam epitaxy growth and optical properties of AlN nanowires. Applied Physics Letters, 2010, 96, .	3.3	49
114	Quantum dot to quantum wire transition ofm-plane GaN islands. Physical Review B, 2009, 79, .	3.2	3
115	GaN/AlGaN intersubband optoelectronic devices. New Journal of Physics, 2009, 11, 125023.	2.9	84
116	The structural properties of GaN insertions in GaN/AlN nanocolumn heterostructures. Nanotechnology, 2009, 20, 295706.	2.6	20
117	Midinfrared intersubband absorption in GaN/AlGaN superlattices on Si(111) templates. Applied Physics Letters, 2009, 95, .	3.3	44
118	CdSe quantum dot in a ZnSe nanowire as an efficient source of single photons. Physica Status Solidi (B): Basic Research, 2009, 246, 846-849.	1.5	0
119	Typeâ€II excitons in ZnTe/ZnSe quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 857-859.	0.8	5
120	Strain effects in GaN/AlN short-period superlattices for intersubband optoelectronics. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S549-S552.	0.8	6
121	Elaboration and optical properties of type-II ZnTe on ZnSe heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 165, 85-87.	3.5	3
122	Type-II ZnTe/ZnSe quantum dots and quantum wells. Superlattices and Microstructures, 2009, 46, 253-257.	3.1	6
123	Bright CdSe quantum dot inserted in single ZnSe nanowires. Microelectronics Journal, 2009, 40, 253-255.	2.0	2
124	CdSe quantum dots in ZnSe nanowires as efficient source for single photons up to 220K. Journal of Crystal Growth, 2009, 311, 2123-2127.	1.5	9
125	Growth and properties of defectâ€free ZnSe nanowires and nanoneedles. Physica Status Solidi (B): Basic Research, 2009, 246, 812-815.	1.5	3
126	Exciton dynamics of a single quantum dot embedded in a nanowire. Physical Review B, 2009, 80, .	3.2	47

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127	Evidence for quantum-confined Stark effect in GaN/AlN quantum dots in nanowires. Physical Review B, 2009, 80, .	3.2	94
128	Strain relaxation in short-period polar GaN/AlN superlattices. Journal of Applied Physics, 2009, 106, 013526.	2.5	56
129	Nucleation mechanism of GaN nanowires grown on (111) Si by molecular beam epitaxy. Nanotechnology, 2009, 20, 415602.	2.6	83
130	A CdSe quantum dot in a ZnSe nanowire as an efficient high-temperature single-photon source. , 2009, , .		0
131	New germanates RCrGeO5 (R=Ndâ€“Er, Y): Synthesis, structure, and properties. Journal of Solid State Chemistry, 2008, 181, 2433-2441.	2.9	11
132	A High-Temperature Single-Photon Source from Nanowire Quantum Dots. Nano Letters, 2008, 8, 4326-4329.	9.1	104
133	Exciton and Biexciton Luminescence from Single GaN/AlN Quantum Dots in Nanowires. Nano Letters, 2008, 8, 2092-2096.	9.1	97
134	Near infrared quantum cascade detector in GaNâˆ•AlGaNâˆ•AlN heterostructures. Applied Physics Letters, 2008, 92, .	3.3	116
135	High-speed operation of GaN/AlGaN quantum cascade detectors at Î»â‰ˆ1.55â€‚Î¼m. Applied Physics Letters, 2008, 93, .	3.3	52
136	Defect-free ZnSe nanowire and nanoneedle nanostructures. Applied Physics Letters, 2008, 93, 143106.	3.3	34
137	Negative magnetopolarization in thermally annealed self-assembled quantum dots. Physical Review B, 2008, 77, .	3.2	11
138	Anisotropic strain state of the [11Â¯00] GaN quantum dots and quantum wires. Journal of Applied Physics, 2008, 104, 063521.	2.5	3
139	Optical properties of m-plane GaN quantum dots and quantum wires. Journal of Applied Physics, 2008, 104, .	2.5	18
140	Measuring local lattice polarity in AlN and GaN by high resolution Z-contrast imaging: The case of (0001) and (11Â¯00) GaN quantum dots. Applied Physics Letters, 2008, 92, .	3.3	17
141	Molecular Beam Epitaxy Growth of ZnTe/ZnSe Type-II Quantum Dots. Journal of the Korean Physical Society, 2008, 53, 137-140.	0.7	0
142	CdSe quantum dot formation: alternative paths to relaxation of a strained CdSe layer and influence of the capping conditions. Nanotechnology, 2007, 18, 265701.	2.6	9
143	Anisotropic strain relaxation in a-plane GaN quantum dots. Journal of Applied Physics, 2007, 101, 063541.	2.5	24
144	Self-assembly of CdSeâˆ•ZnSe(001) quantum dot structures mediated by a tellurium cap layer. Applied Physics Letters, 2007, 91, 153110.	3.3	15

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145	Growth of m-plane GaN quantum wires and quantum dots on m-plane 6H-SiC. Journal of Applied Physics, 2007, 102, 074913.	2.5	18
146	Spin ladder compoundPb0.55Cd0.45V2O5: Synthesis and investigation. Physical Review B, 2007, 76, .	3.2	1
147	Anisotropic morphology of nonpolar a-plane GaN quantum dots and quantum wells. Journal of Applied Physics, 2007, 102, 074304.	2.5	37
148	PITTONGITE, A NEW TUNGSTATE WITH A MIXED-LAYER, PYROCHLORE HEXAGONAL TUNGSTEN BRONZE STRUCTURE, FROM VICTORIA, AUSTRALIA. Canadian Mineralogist, 2007, 45, 857-864.	1.0	8
149	CdSe quantum dot formation induced by amorphous Se. Surface Science, 2007, 601, 2664-2666.	1.9	0
150	Structural and optical properties of CdSe quantum dots induced by amorphous Se. Journal of Crystal Growth, 2007, 301-302, 281-284.	1.5	9
151	Chemical twinning of the pyrochlore structure in the system Bi2O3â€“Fe2O3â€“Nb2O5. Journal of Solid State Chemistry, 2007, 180, 158-166.	2.9	9
152	Inserting one single Mn ion into a quantum dot. Applied Physics Letters, 2006, 89, 193109.	3.3	43
153	Morphology of CdSe/ZnSe quantum dots grown by MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 938-941.	0.8	6
154	Tuning the magnetic properties of ZnCdSe/ZnSe quantum dots by thermal annealing. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3904-3907.	0.8	0
155	Inserting one single Mn ion into a quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3992-3996.	0.8	4
156	Control of single spins in individual magnetic quantum dots. Physica Status Solidi (B): Basic Research, 2006, 243, 3709-3718.	1.5	4
157	Unit-cell intergrowth of pyrochlore and hexagonal tungsten bronze structures in secondary tungsten minerals. Journal of Solid State Chemistry, 2006, 179, 3860-3869.	2.9	21
158	Elastic and surface energies: Two key parameters for CdSe quantum dot formation. Applied Physics Letters, 2006, 88, 233103.	3.3	27
159	Synthesis and structure investigation of the Pb3V(PO4)3 eulytite. Journal of Solid State Chemistry, 2005, 178, 3715-3721.	2.9	20
160	Properties of Ga1â^'xMnxN Epilayers Grown by Molecular Beam Epitaxy. AIP Conference Proceedings, 2005, , .	0.4	0
161	Structure of LaCuO2.66: an oxidized delafossite compound containing hole-doped kagome planes of Cu2+ cations. Solid State Sciences, 2003, 5, 1095-1104.	3.2	25
162	Fe and Co Nanowires and Nanotubes Synthesized by Template Electrodeposition. Journal of the Electrochemical Society, 2003, 150, E468.	2.9	37

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163	Structure of heavy-metal sorbed birnessite: Part 2. Results from electron diffraction. American Mineralogist, 2002, 87, 1646-1661.	1.9	42
164	Surface quality studies of high-Tc superconductors of the Hg-, Tl- and HgxTl1â^'x-families: RBS and resonant C and O backscattering studies. Nuclear Instruments & Methods in Physics Research B, 2002, 190, 673-678.	1.4	1
165	The superconducting bismuth-based mixed oxides. Current Applied Physics, 2002, 2, 425-430.	2.4	3
166	PbMnO2.75â€"a high-pressure phase having a new type of crystallographic shear structure derived from perovskite. Journal of Solid State Chemistry, 2002, 169, 131-138.	2.9	39
167	Structure determination of oxide compounds by electron crystallography. Micron, 2001, 32, 473-479.	2.2	10
168	CaOâ€"CuO system at high oxygen pressure: bulk synthesis and transport properties of Ca14Cu24O41. Physica C: Superconductivity and Its Applications, 2001, 351, 301-307.	1.2	4
169	Crystal structure of high-Tc related NdBaCuO2BO3: TEM and neutron powder diffraction study. Physica C: Superconductivity and Its Applications, 2001, 355, 119-125.	1.2	4
170	Effects of Re substitution on the structure and superconductivity of Cu1â^'xRexBa2YCu2Ow. Physica C: Superconductivity and Its Applications, 2001, 355, 267-277.	1.2	1
171	The Fine Structure of YCuO2+x Delafossite Determined by Synchrotron Powder Diffraction and Electron Microscopy. Journal of Solid State Chemistry, 2001, 156, 428-436.	2.9	39
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